



BAV70

SWITCHING DIODE 開關二極管(BAV70)

■FEATURES 特點

Characteristic 特性參數	Symbol 符號	Max 最大值	Unit 單位
Power dissipation 耗散功率	$P_D(T_a=25^\circ\text{C})$	225	mW
Forward Current 正向電流	I_F	200	mA
Reverse Voltage 反向電壓	V_R	70	V
Junction and Storage Temperature 結溫和儲藏溫度	T_J, T_{stg}	-55to+150°C	

■DEVICE MARKING 打標

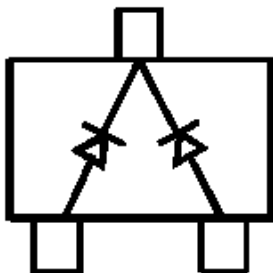
BAV70=A4

■ELECTRICAL CHARACTERISTICS 電特性

($T_A=25^\circ\text{C}$ unless otherwise noted 如無特殊说明，溫度為 25°C)

Characteristic 特性參數	Symbol 符號	Min 最小值	Max 最大值	Unit 單位
Reverse Breakdown Voltage 反向擊穿電壓 ($I_R=100\mu\text{A}$)	$V_{(BR)}$	70	—	V
Reverse Leakage Current 反向漏電流 ($V_R=70\text{V}$)	I_R	—	1	μA
Forward Voltage(Test Condition)正向電壓 $I_F=1\text{mA}$ $I_F=10\text{mA}$ $I_F=50\text{mA}$ $I_F=150\text{mA}$	V_F		715 855 1000 1250	mV
Diode Capacitance 二極體電容 ($V_R=0\text{V}, f=1\text{MHz}$)	C_D	—	1.5	pF
Reverse Recovery Time 反向恢復時間	T_{rr}	—	6	nS

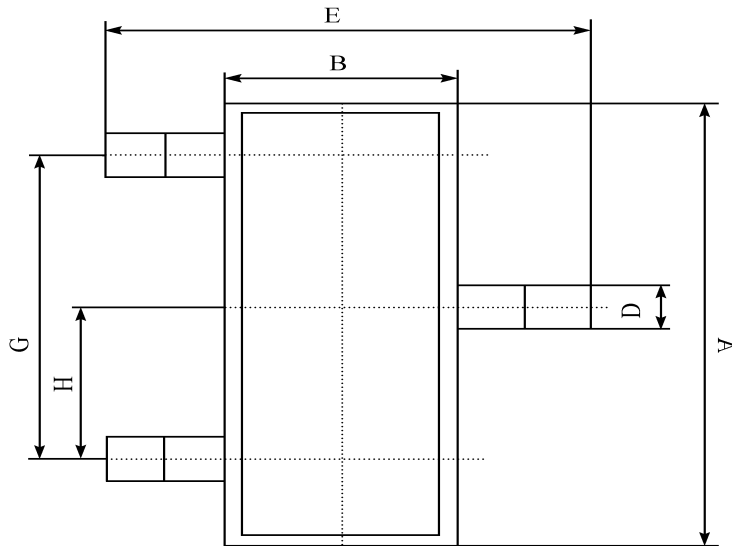
■SOT-23 内部结构



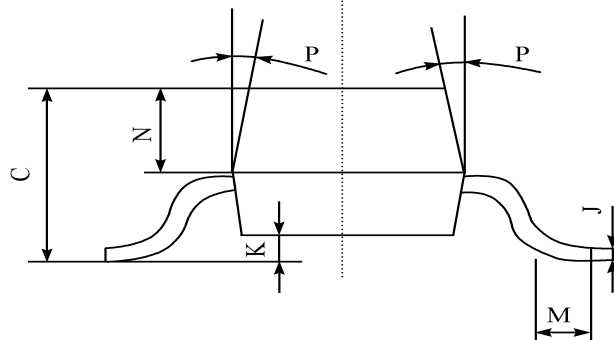


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■ DIMENSION 外形封裝尺寸



序號	數值及公差
A	2.90 ± 0.10
B	1.30 ± 0.10
C	1.00 ± 0.10
D	0.40 ± 0.10
E	2.40 ± 0.20
G	1.90 ± 0.10
H	0.95 ± 0.05
J	0.13 ± 0.05
K	$0.00 - 0.10$
M	≥ 0.2
N	0.60 ± 0.10
P	$7 \pm 2^\circ$



This datasheet presents technical data of Tak Cheong's Silicon Rectifier Diodes. Complete specifications for the individual devices are provided in the form of datasheets. A comprehensive Selector Guide is included to simplify the task of choosing the best set of components required for a specific application. For additional information, please visit our website <http://www.takcheong.com>.

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